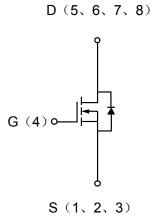


N-Channel MOSFET

Description

The N-channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low on-resistance and fast switching speed.

MOSFET Product Summary			
V _{DS} (V)	$R_{DS(on)}(m \Omega)$	I _D (A)	
30	12@ V _{GS} =10V	12.0	
	17@ V _{GS} =4.5V	12.0	



Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	$I_D = 250 \mu A, V_{GS} = 0 V$	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V,V _{GS} =±20V	-	-	±100	nA	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 10$ mA	1.0	1.5	2.5	V	
	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	12	18	mΩ	
Static Drain-Source On-Resistance		V _{GS} =4.5V, I _D =10A	-	17	24	mΩ	
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0V, I _S =1A	-	0.65	1	V	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}		-	900	1150	pF	
Output Capacitance	C _{DSS}	V _{GS} =0V, V _{DS} =15V, f=1MHz	-	135		pF	
Reverse Transfer Capacitance	C _{RSS}	1-1101112	-	100		pF	
SWITCHING PARAMETERS							
Turn-On Delay Time	t _{d(on)}	V _{DS} =15V, V _{GS} =10V,	-		7.5	ns	
Turn-Off Delay Time	$t_{\text{d(off)}}$	$R_L=1.3\Omega$, $R_G=3\Omega$	-		20	ns	

Absolute maximum rating@25℃

Rating		Symbol	Value	Units	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Drain Current	Continuous	I _D	12.0	А	
	Pulsed	I _D	55	Α	
Total Power Dissipation	T _A =25℃	P _D	3.2	W	
	T _A =125℃	P _D	2.5	W	

Typical Characteristics

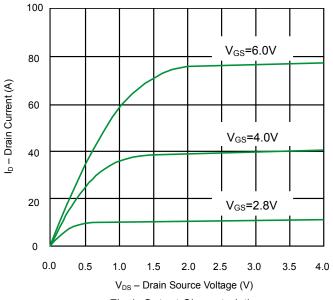


Fig 1. Output Characteristics

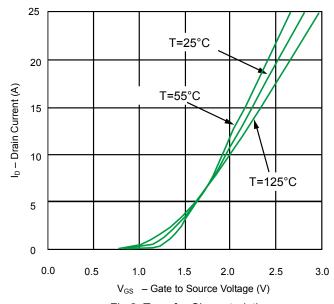


Fig 2. Transfer Characteristics

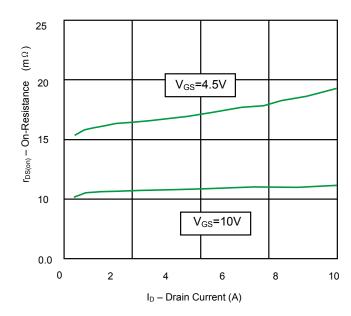


Fig 3. On-Resistance vs. Drain Current

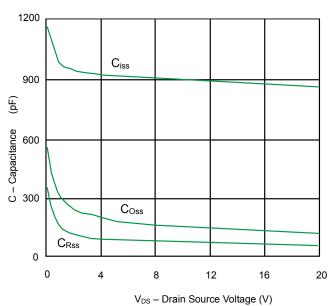
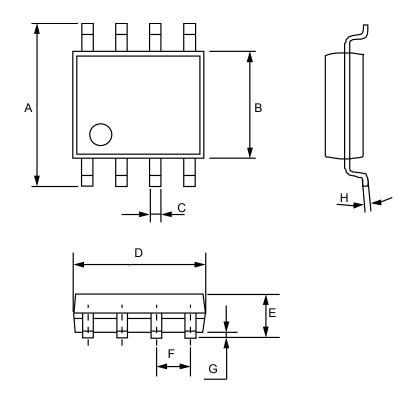


Fig 4. Capacitance

Product dimension (SOP-8)



Dim	Millimeters		Inches		
	MIN	MAX	MIN	MAX	
А	5.800	6.200	0.228	0.244	
В	3.800	4.000	0.150	0.157	
С	0.330	0.510	0.013	0.020	
D	4.700	5.100	0.185	0.200	
Е	1.350	1.750	0.053	0.069	
F	1.270 (BSC)		0.050 (BSC)		
G	0.100	0.250	0.004	0.010	
Н	0.170	0.250	0.006	0.010	

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